



FDMS86255ET150

N-Channel Shielded Gate PowerTrench[®] MOSFET

150 V, 63 A, 12.4 mΩ

Features

- Extended T_J rating to 175°C
- Shielded Gate MOSFET Technology
- Max r_{DS(on)} = 12.4 mΩ at V_{GS} = 10 V, I_D = 10 A
- Max r_{DS(on)} = 15.5 mΩ at V_{GS} = 6 V, I_D = 8 A
- Advanced Package and Silicon combination for low r_{DS(on)} and high efficiency
- Next generation enhanced body diode technology, engineered for soft recovery
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

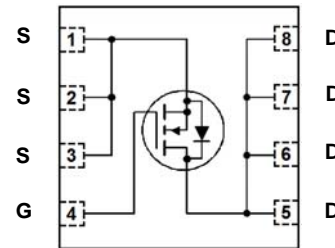
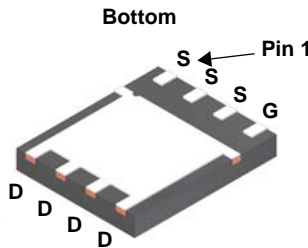
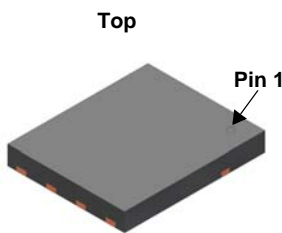


General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance.

Applications

- OringFET / Load Switching
- Synchronous rectification
- DC-DC Conversion



Power 56

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DS}	Drain to Source Voltage	150	V
V _{GS}	Gate to Source Voltage	±20	V
I _D	Drain Current -Continuous T _C = 25 °C (Note 5)	63	A
	-Continuous T _C = 100°C (Note 5)	44	
	-Continuous T _A = 25 °C (Note 1a)	10	
	-Pulsed (Note 4)	276	
E _{AS}	Single Pulse Avalanche Energy (Note 3)	541	mJ
P _D	Power Dissipation T _C = 25 °C	136	W
	Power Dissipation T _A = 25 °C (Note 1a)	3.3	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +175	°C

Thermal Characteristics

R _{θJC}	Thermal Resistance, Junction to Case	1.1	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient (Note 1a)	45	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS86255ET	FDMS86255ET150	Power 56	13 "	12 mm	3000 units

FDMS86255ET150 N-Channel Shielded Gate PowerTrench[®] MOSFET

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}, V_{GS} = 0\ \text{V}$	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, referenced to 25°C		109		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 120\ \text{V}, V_{GS} = 0\ \text{V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\ \text{V}, V_{DS} = 0\ \text{V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	2.0	3.0	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, referenced to 25°C		-11		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}, I_D = 10\ \text{A}$		9.5	12.4	m Ω
		$V_{GS} = 6\ \text{V}, I_D = 8\ \text{A}$		11.5	15.5	
		$V_{GS} = 10\ \text{V}, I_D = 10\ \text{A}, T_J = 125^\circ\text{C}$		19	25	
g_{FS}	Forward Transconductance	$V_{DS} = 5\ \text{V}, I_D = 10\ \text{A}$		35		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 75\ \text{V}, V_{GS} = 0\ \text{V},$ $f = 1\ \text{MHz}$		3200	4480	pF
C_{oss}	Output Capacitance			291	410	pF
C_{rss}	Reverse Transfer Capacitance			11	20	pF
R_g	Gate Resistance		0.1	0.7	2.1	Ω

Switching Characteristics

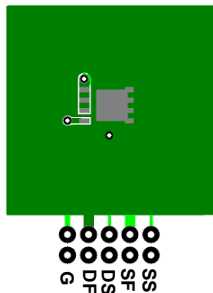
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75\ \text{V}, I_D = 10\ \text{A},$ $V_{GS} = 10\ \text{V}, R_{GEN} = 6\ \Omega$		21	34	ns	
t_r	Rise Time			4.5	10	ns	
$t_{d(off)}$	Turn-Off Delay Time			28	45	ns	
t_f	Fall Time			6.2	12	ns	
Q_g	Total Gate Charge		$V_{GS} = 0\ \text{V to } 10\ \text{V}$		45	63	nC
Q_g	Total Gate Charge		$V_{GS} = 0\ \text{V to } 6\ \text{V}$		29	41	nC
Q_{gs}	Gate to Source Charge	$V_{DD} = 75\ \text{V},$ $I_D = 10\ \text{A}$		14		nC	
Q_{gd}	Gate to Drain "Miller" Charge			8.8		nC	

Drain-Source Diode Characteristics

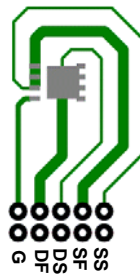
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\ \text{V}, I_S = 1.9\ \text{A}$ (Note 2)		0.7	1.2	V
		$V_{GS} = 0\ \text{V}, I_S = 10\ \text{A}$ (Note 2)		0.8	1.3	
t_{rr}	Reverse Recovery Time	$I_F = 10\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		87	139	ns
Q_{rr}	Reverse Recovery Charge			165	264	nC

Notes:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



a. $45^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper.



b. $115^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. E_{AS} of 541 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 3\ \text{mH}$, $I_{AS} = 19\ \text{A}$, $V_{DD} = 150\ \text{V}$, $V_{GS} = 10\ \text{V}$. 100% tested at $L = 0.1\ \text{mH}$, $I_{AS} = 60\ \text{A}$.

4. Pulse I_d please refer to Fig.11 SOA curve for detail.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

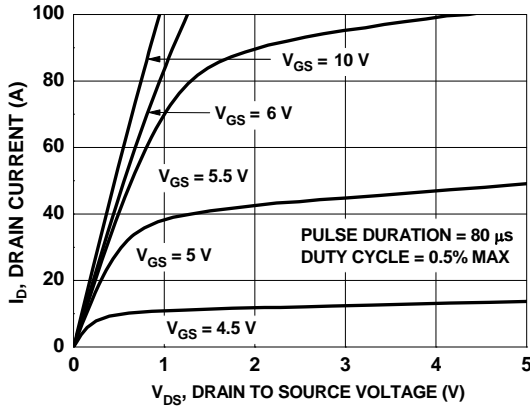


Figure 1. On-Region Characteristics

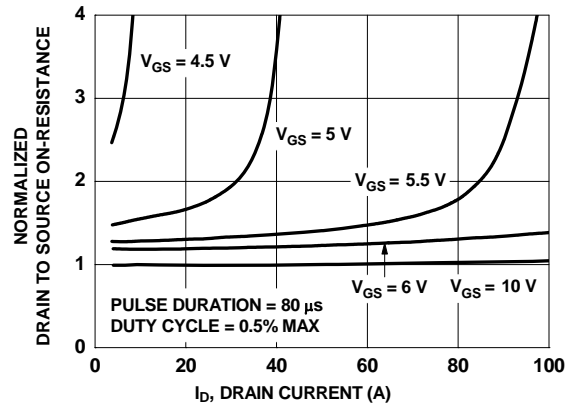


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

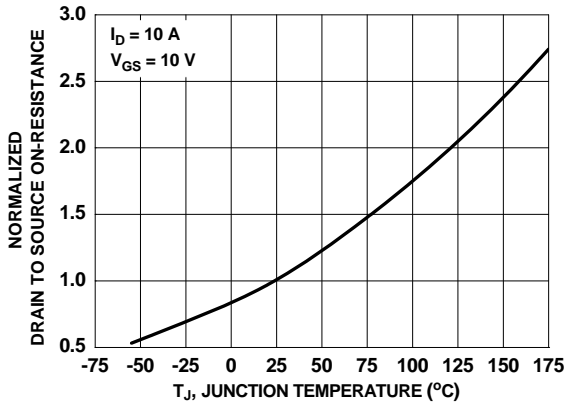


Figure 3. Normalized On-Resistance vs Junction Temperature

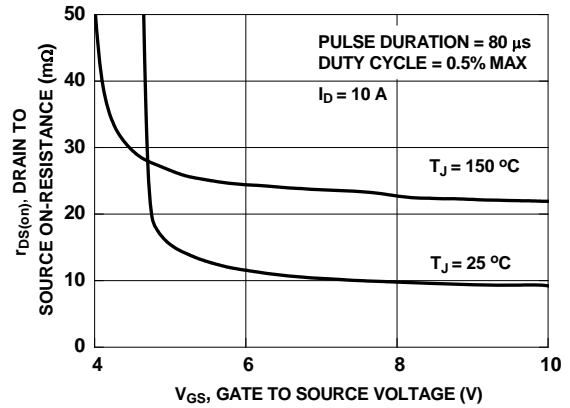


Figure 4. On-Resistance vs Gate to Source Voltage

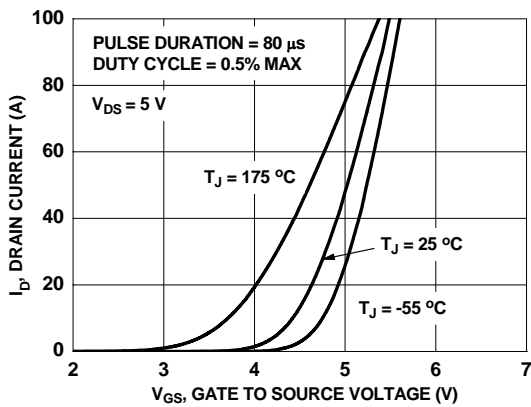


Figure 5. Transfer Characteristics

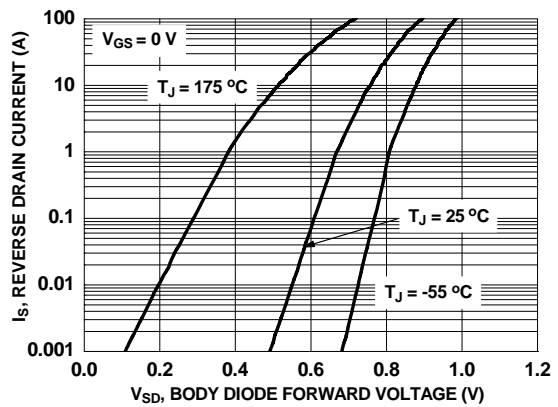


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

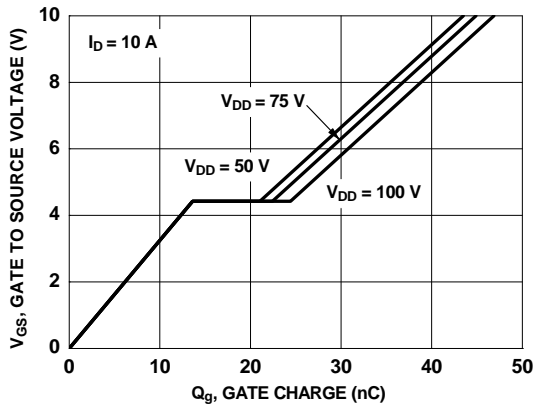


Figure 7. Gate Charge Characteristics

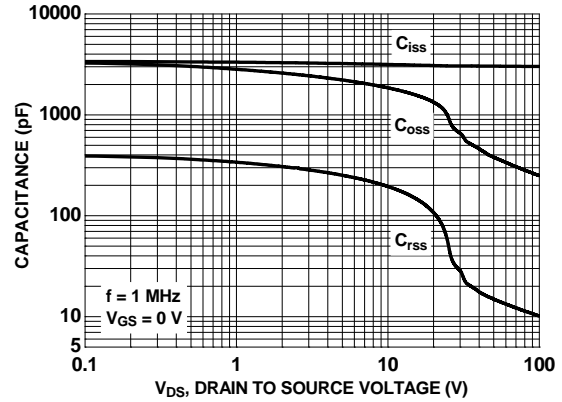


Figure 8. Capacitance vs Drain to Source Voltage

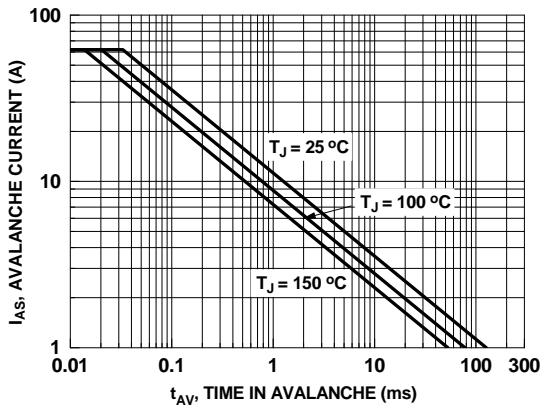


Figure 9. Unclamped Inductive Switching Capability

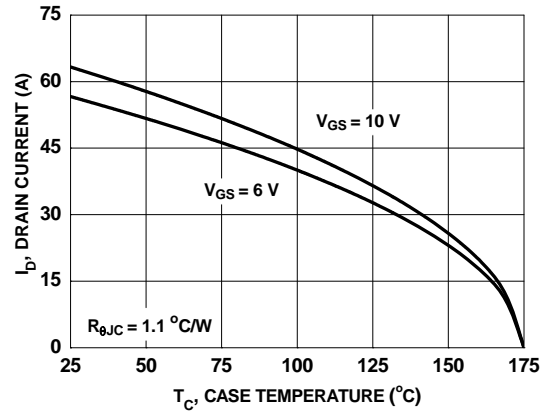


Figure 10. Maximum Continuous Drain Current vs Case Temperature

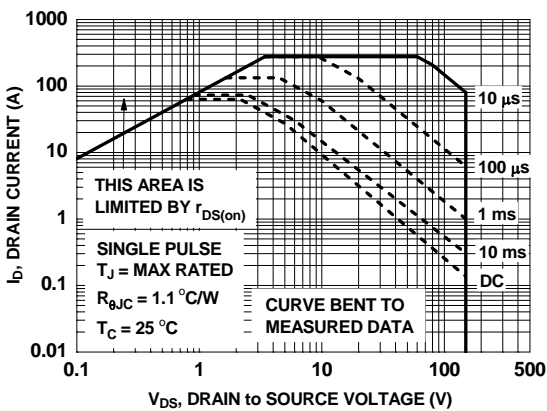


Figure 11. Forward Bias Safe Operating Area

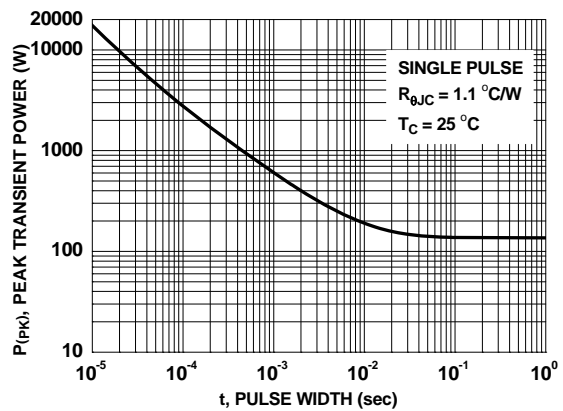
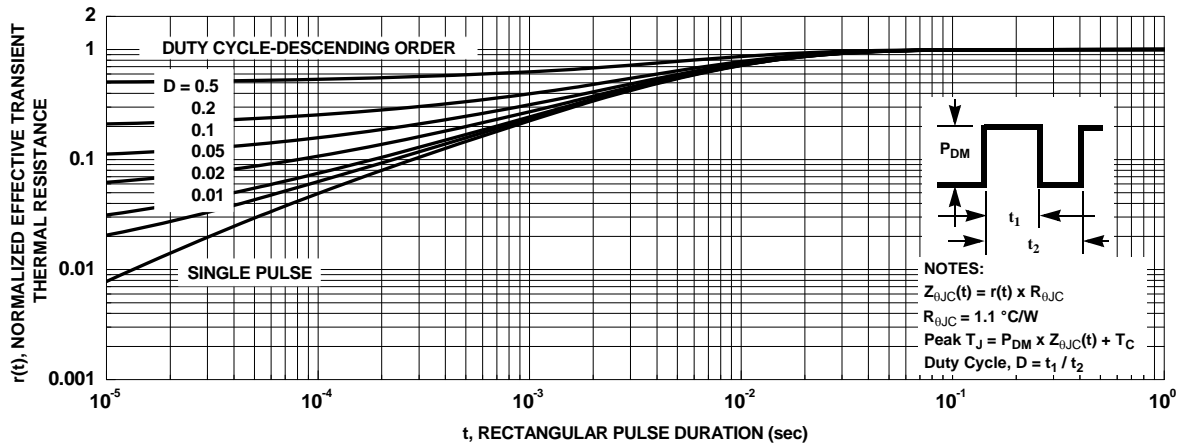
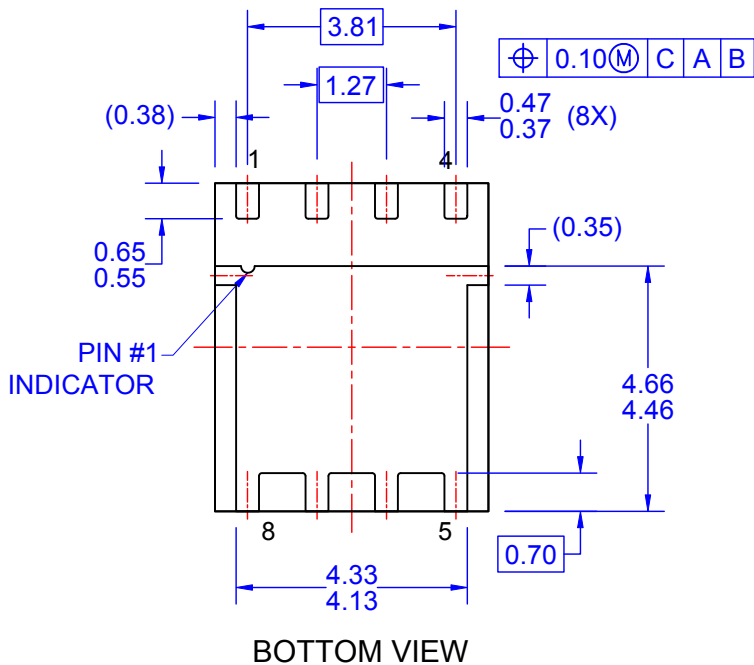
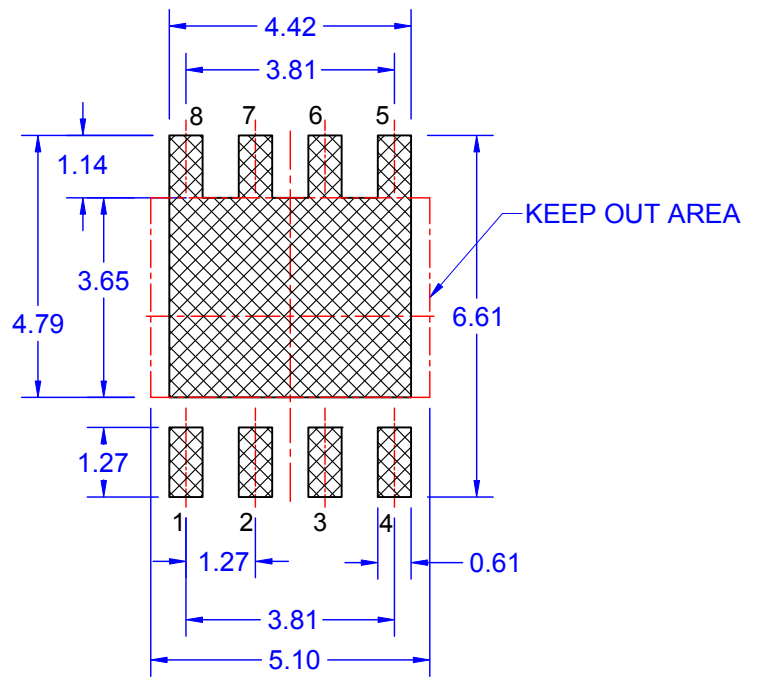
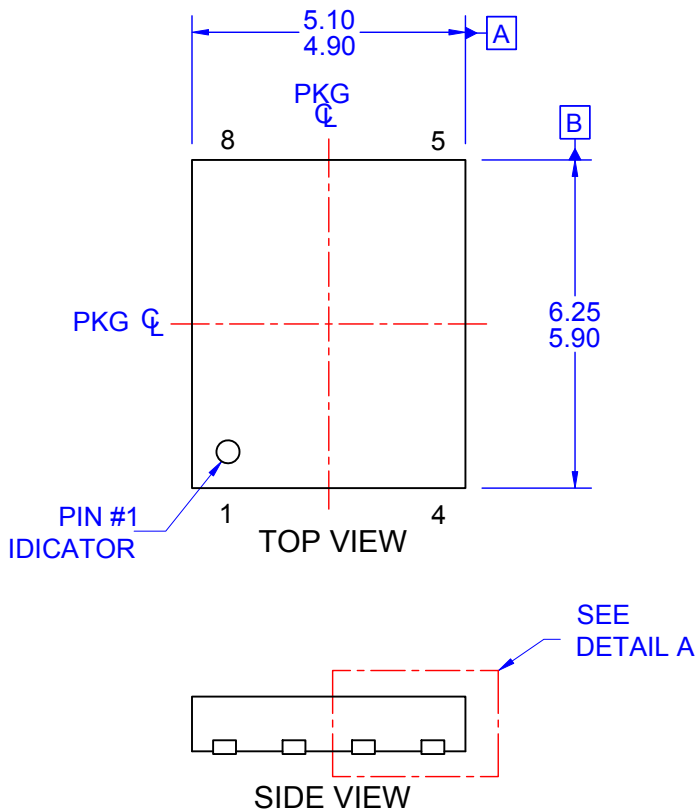


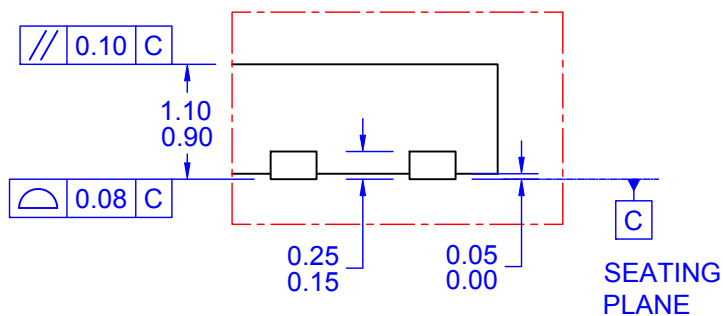
Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted





- NOTES: UNLESS OTHERWISE SPECIFIED
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DETAIL A
SCALE: 2:1



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